Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS302PZ

2. Features and benefits

- · Low collector-emitter saturation voltage VCEsat
- · High collector current capability IC and ICM
- · High collector current gain (hFE) at high IC
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Charging circuits
- · Power switches (e.g. fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	5.8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	11.6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	30	43	mΩ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	E	emitter		B——
4	С	collector	□ 1 □ 2 □ 3	Ė
			SC-73 (SOT223)	sym123



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6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS302NZ	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS302NZ	S302NZ

8. Limiting values

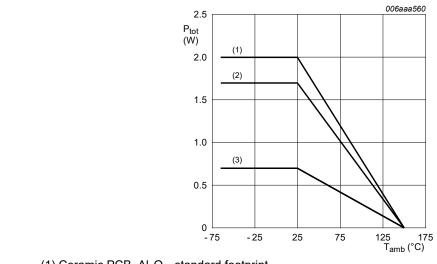
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	5.8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	11.6	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

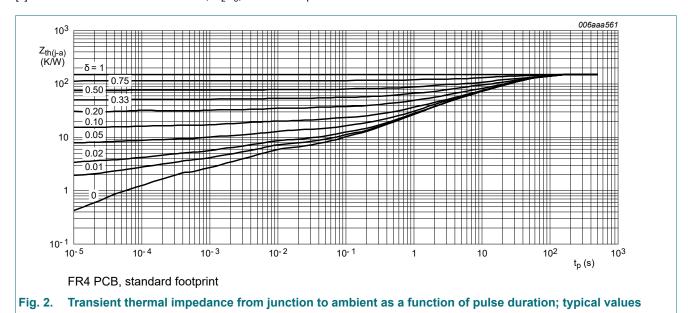
Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	179	K/W
		[2]	-	-	74	K/W	
			[3]	-	-	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	15	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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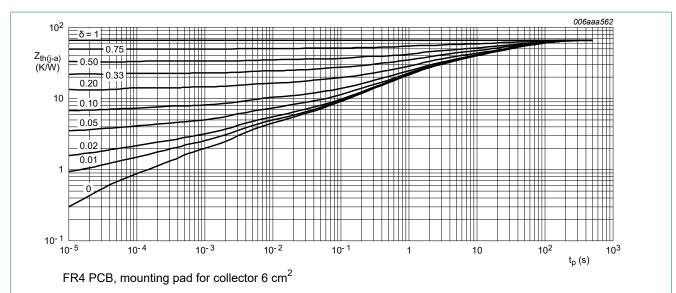


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

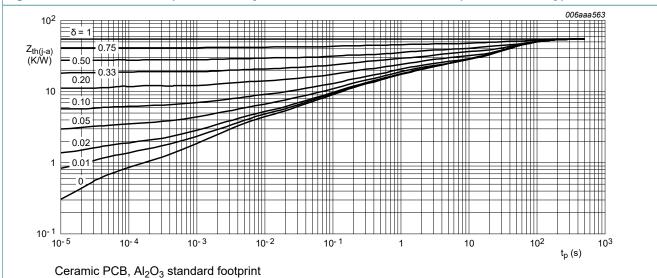


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	570	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	300	550	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	250	520	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	450	-	
		V_{CE} = 2 V; I_{C} = 7 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	350	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	20	25	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	35	50	mV
		I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	50	70	mV
		I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	70	100	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	120	170	mV
		I_C = 4 A; I_B = 400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	115	165	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	155	240	mV
		I_C = 5.8 A; I_B = 290 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	170	250	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	30	43	mΩ
		I_C = 4 A; I_B = 40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	38	60	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.82	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.92	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.75	0.85	V
d	delay time	V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 0.15 A;	-	15	-	ns
·r	rise time	I _{Boff} = -0.15 A; T _{amb} = 25 °C	-	40	-	ns
on	turn-on time		-	55	-	ns
s	storage time	1	-	270	-	ns
f	fall time	1	-	85	-	ns
off	turn-off time	1	-	335	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	95	150	pF

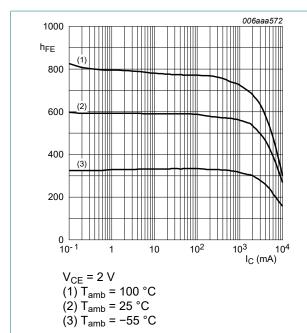


Fig. 5. DC current gain as a function of collector current; typical values

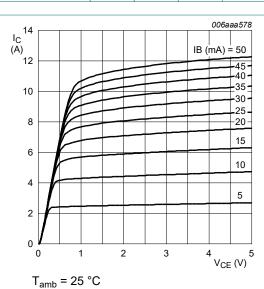
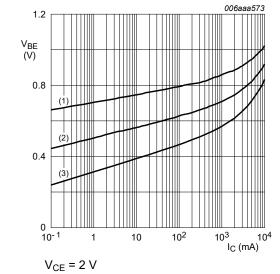


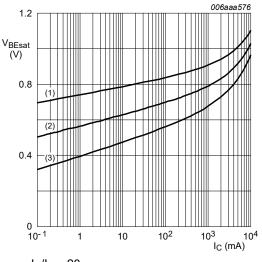
Fig. 6. Collector current as a function of collectoremitter voltage; typical values



(1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

 $(3) T_{amb} = 100 °C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) T_{amb} = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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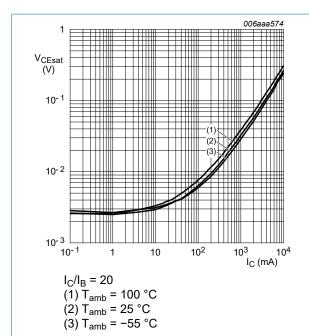


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

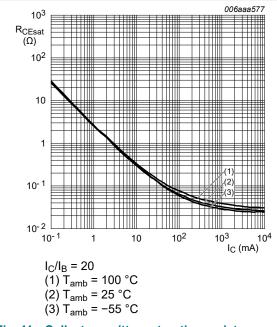


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

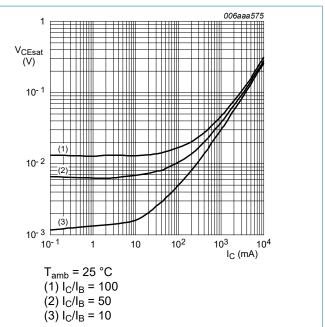


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

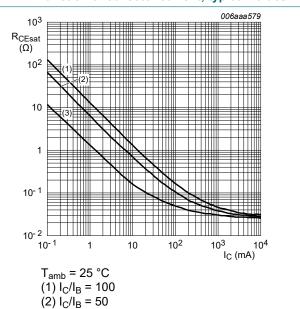
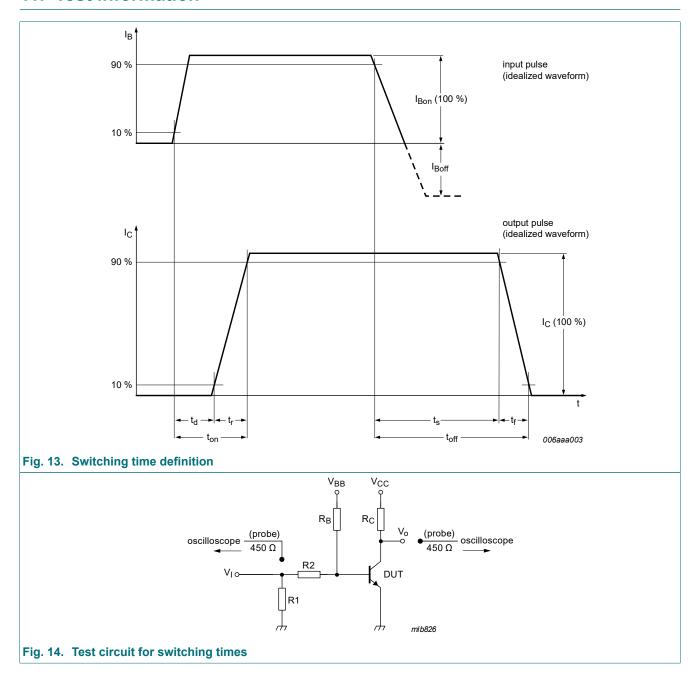


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

(3) $I_C/I_B = 10$

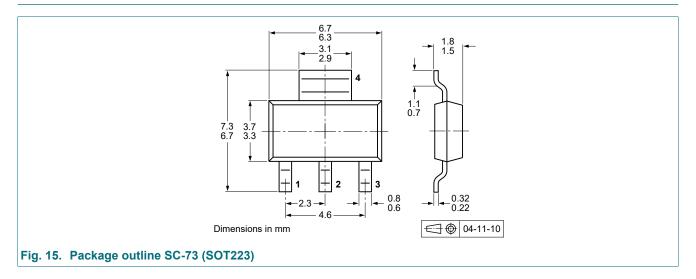
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11. Test information

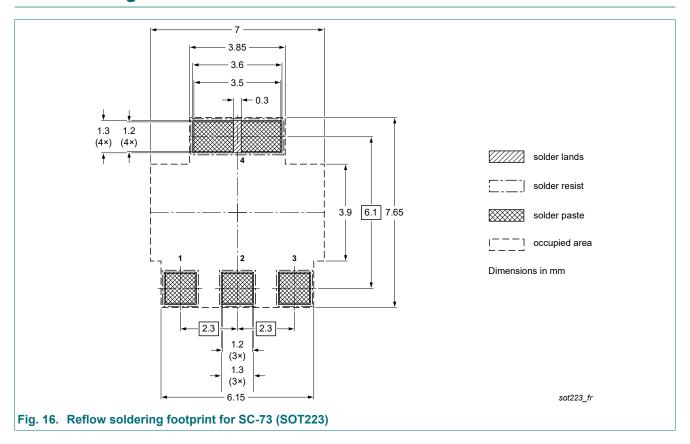


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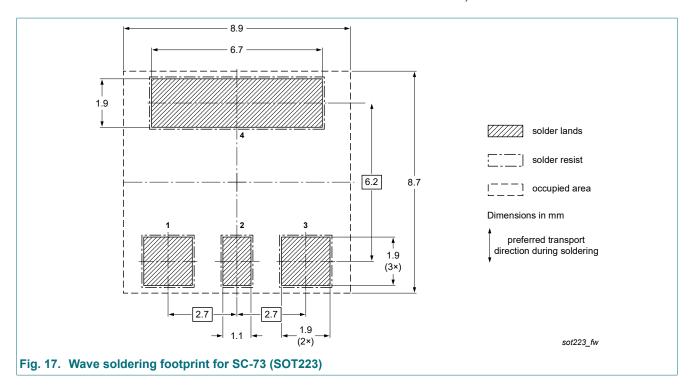
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Tuble 6. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS302NZ v.4	20241008	Product data sheet	-	PBSS302NZ v.3			
Modifications:		 Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). 					
PBSS302NZ v.3	20230112	Product data sheet	-	PBSS302NZ_2			
PBSS302NZ_2	20091120	Product data sheet	-	PBSS302NZ_1			
PBSS302NZ_1	20060908	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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